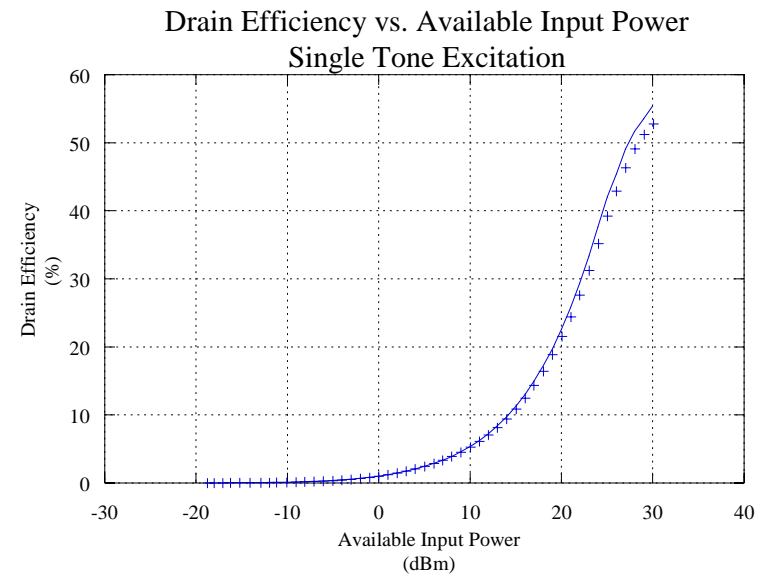
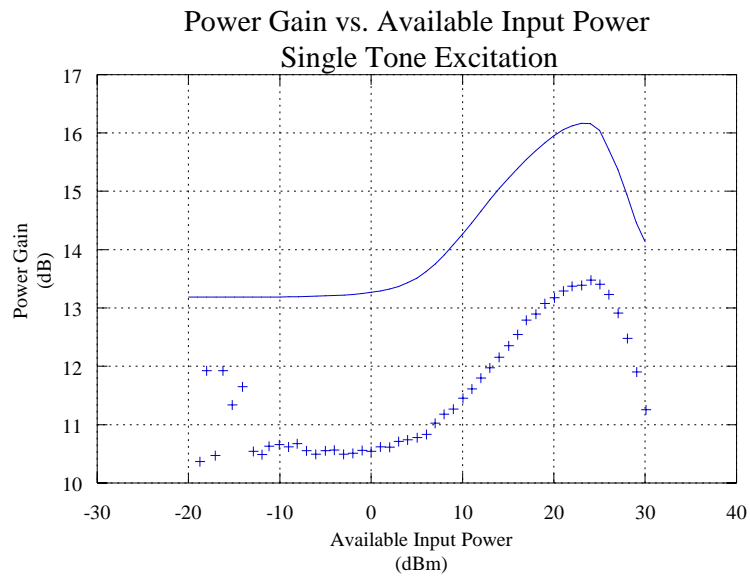
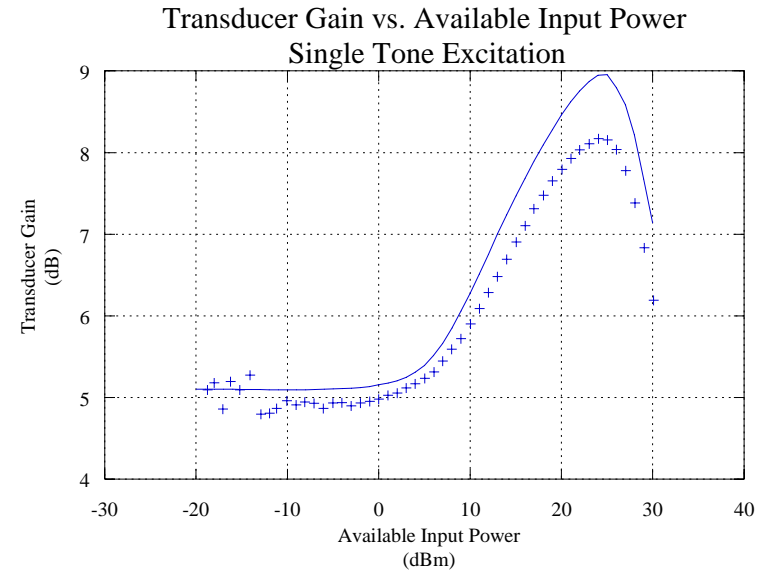
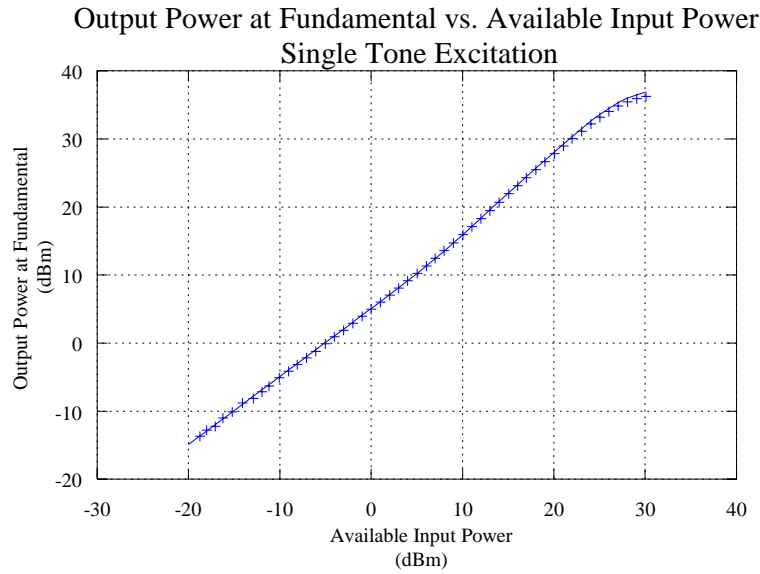


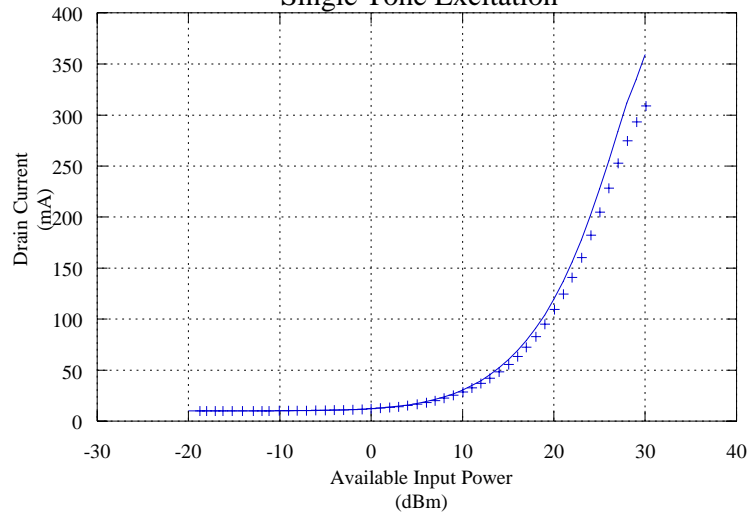
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm  
 50 ohm Termination  
 Solid: Simulated & Points: Measured



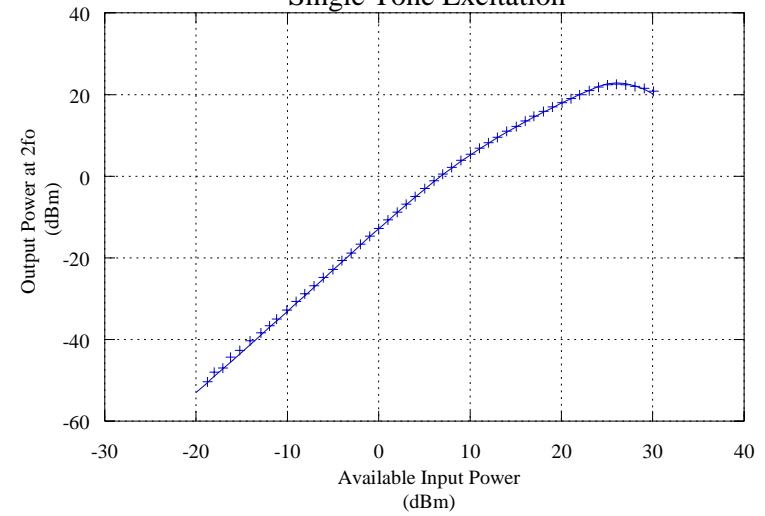
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm

50 ohm Termination  
 Solid: Simulated & Points: Measured

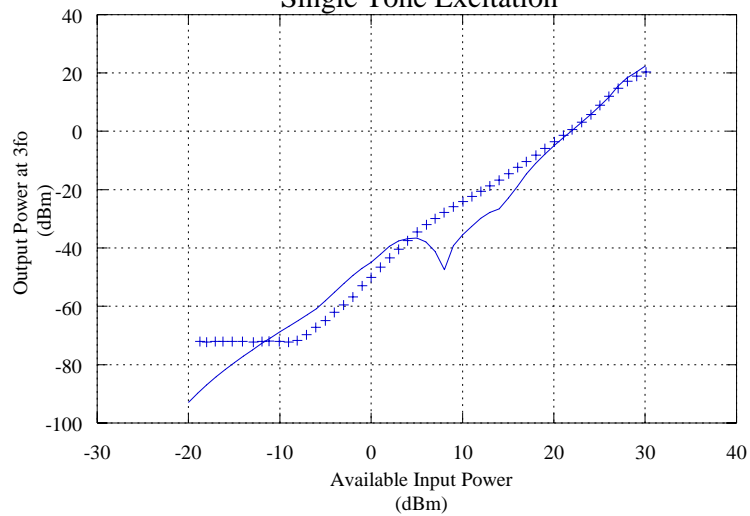
Drain Current vs. Available Input Power  
 Single Tone Excitation



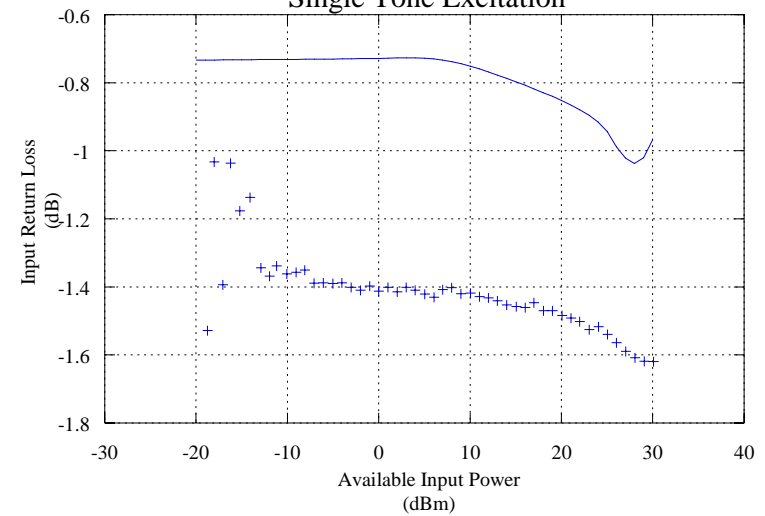
Output Power at 2fo vs. Available Input Power  
 Single Tone Excitation



Output Power at 3fo vs. Available Input Power  
 Single Tone Excitation



Input Return Loss vs. Available Input Power  
 Single Tone Excitation

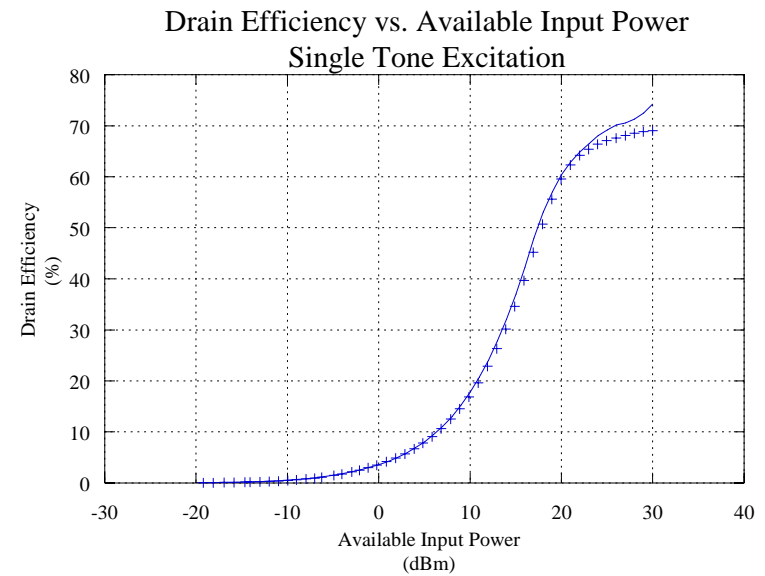
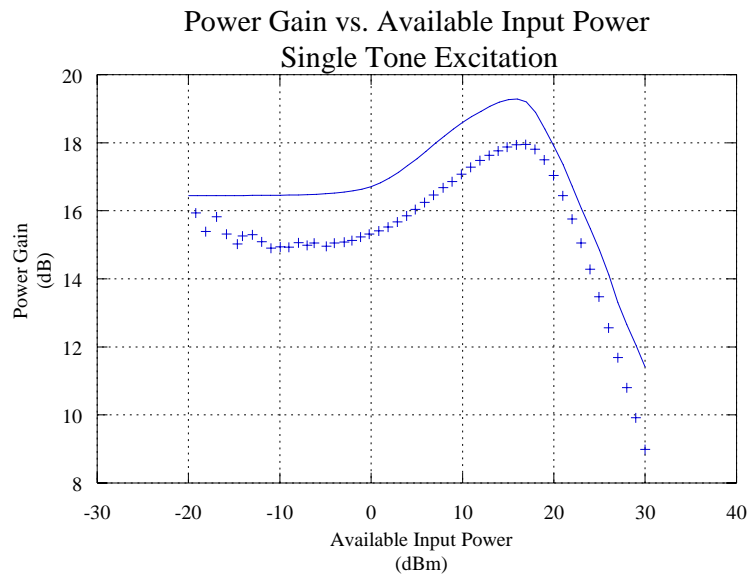
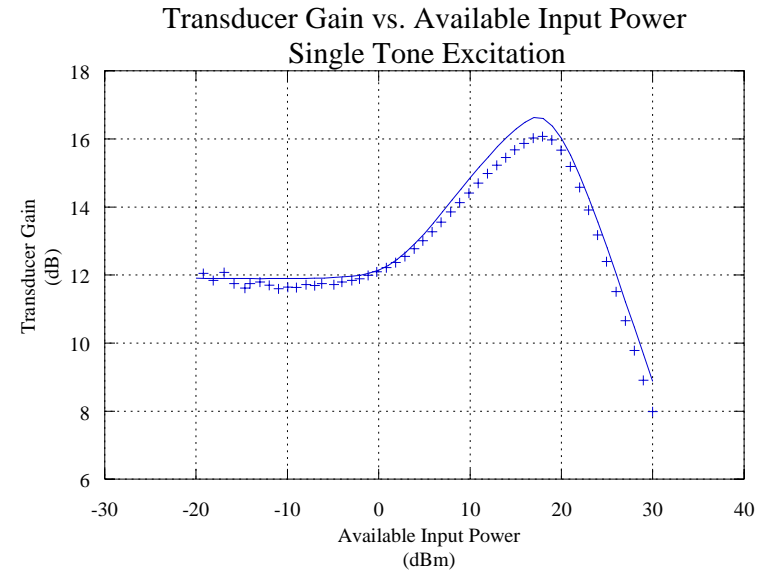
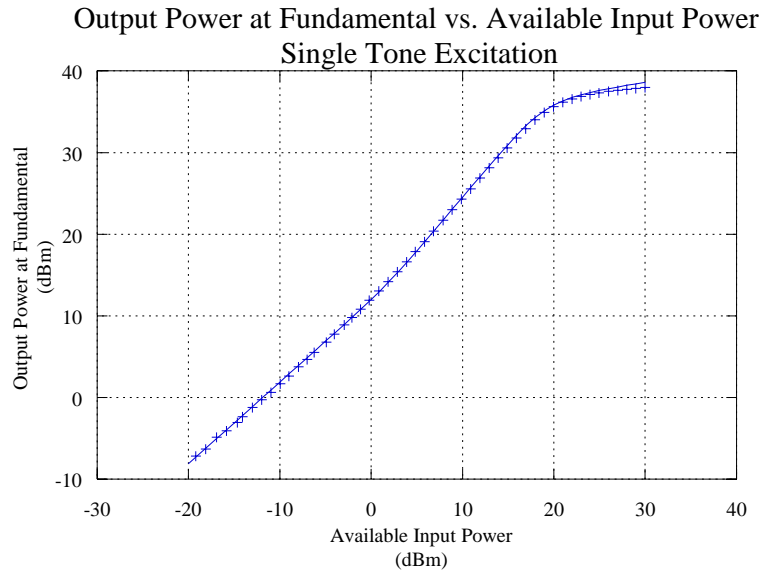




1 Block HV1 LDMOS Device  
Number of fingers: 56, Periphery: 5.04 mm  
Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm



Tuned for Power  
Solid: Simulated & Points: Measured



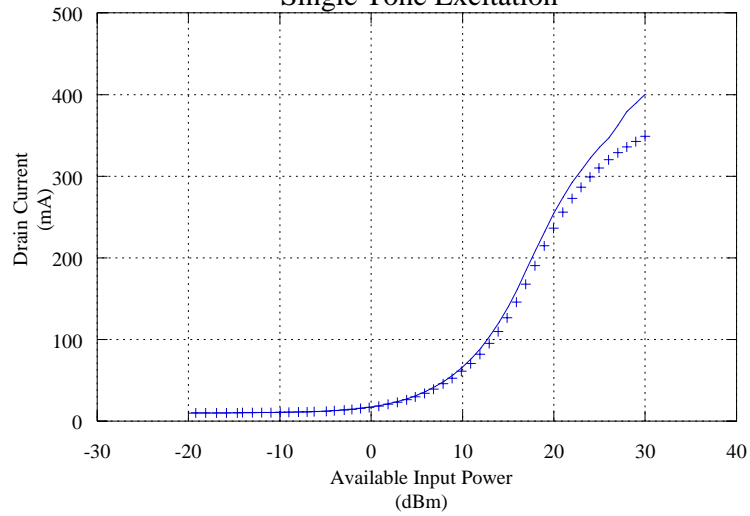


1 Block HV1 LDMOS Device  
Number of fingers: 56, Periphery: 5.04 mm  
Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm

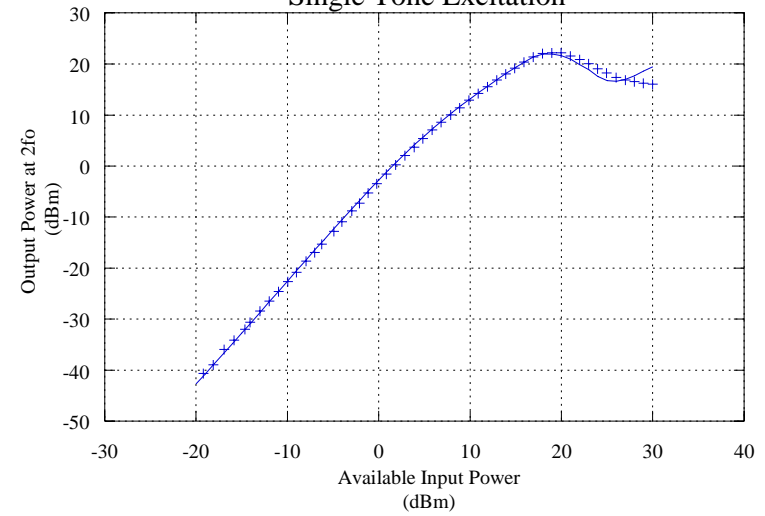


Tuned for Power  
Solid: Simulated & Points: Measured

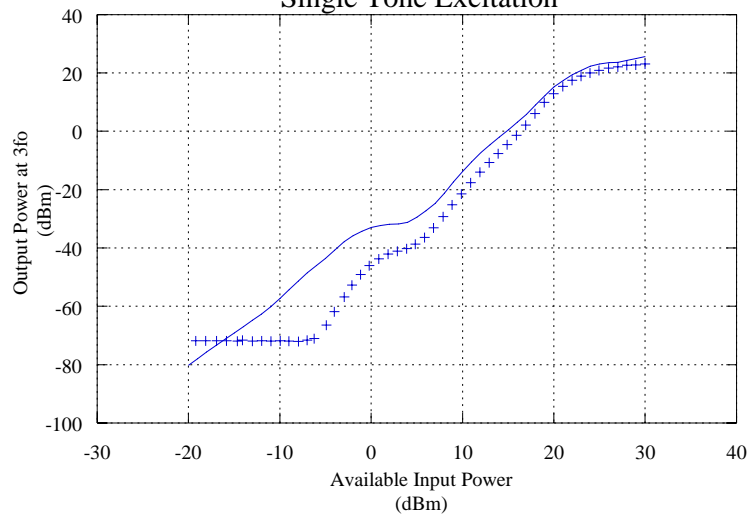
Drain Current vs. Available Input Power  
Single Tone Excitation



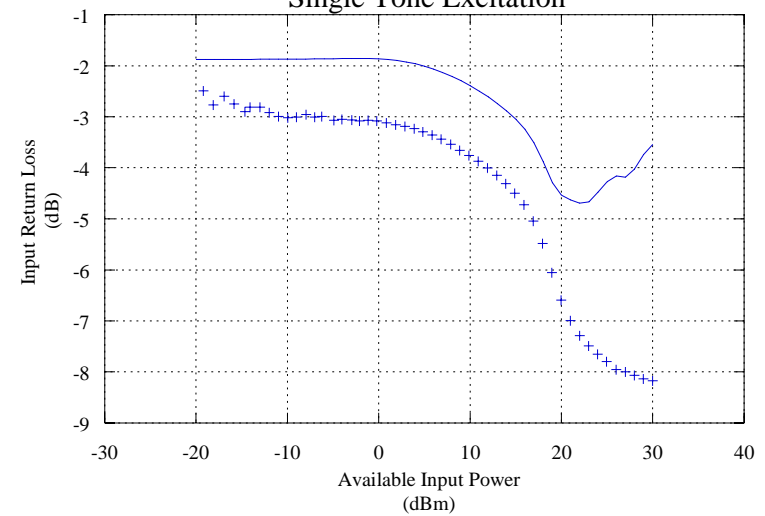
Output Power at 2fo vs. Available Input Power  
Single Tone Excitation



Output Power at 3fo vs. Available Input Power  
Single Tone Excitation

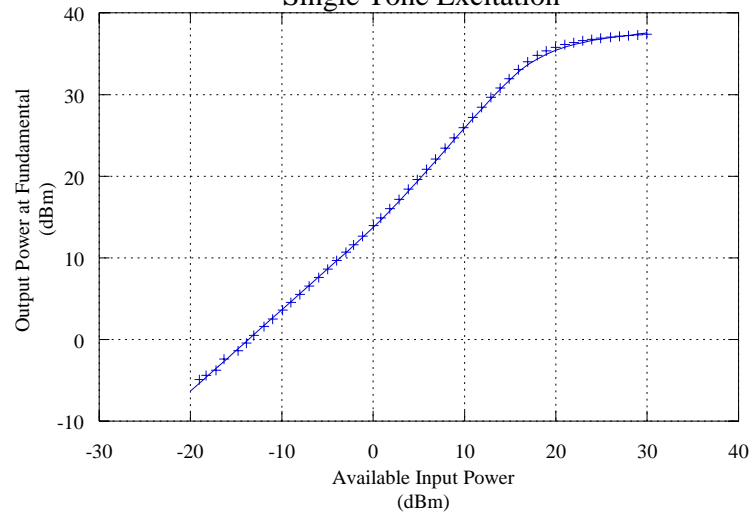


Input Return Loss vs. Available Input Power  
Single Tone Excitation

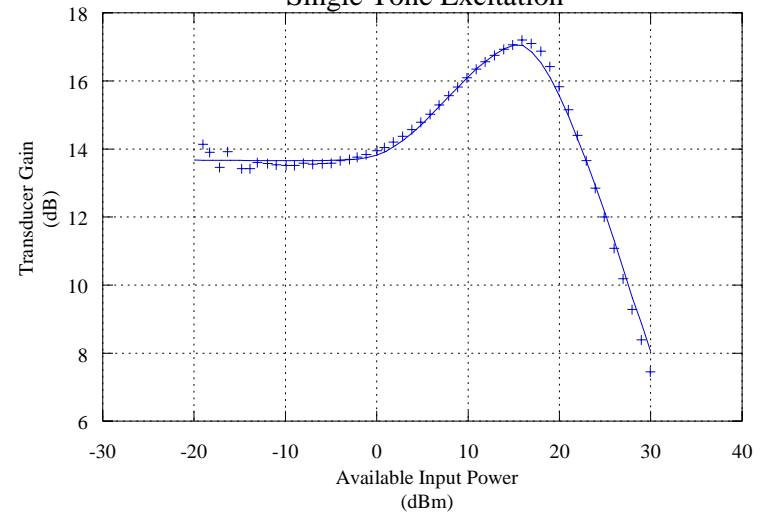


Tuned for Efficiency  
 Solid: Simulated & Points: Measured

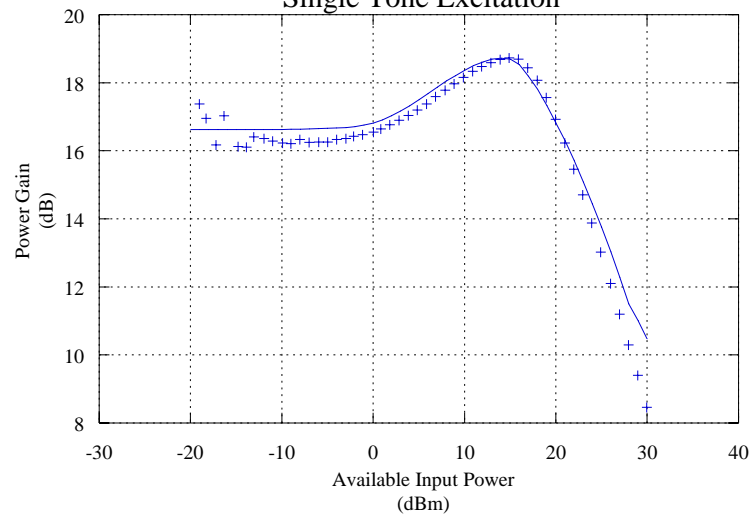
Output Power at Fundamental vs. Available Input Power  
 Single Tone Excitation



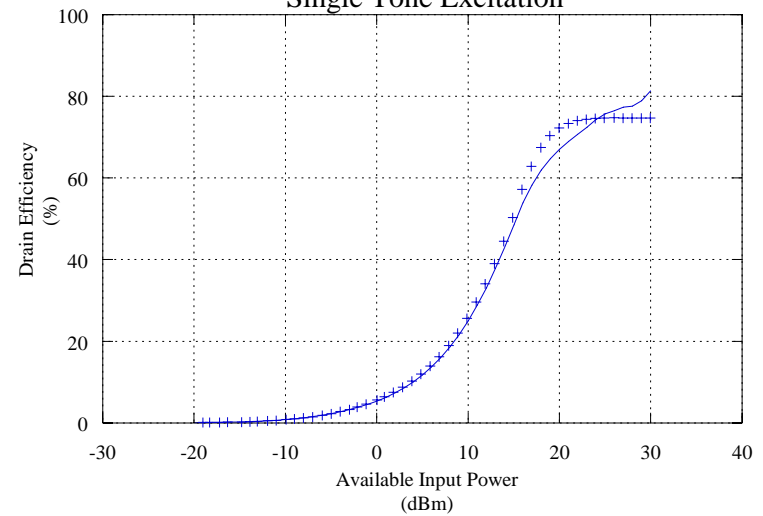
Transducer Gain vs. Available Input Power  
 Single Tone Excitation



Power Gain vs. Available Input Power  
 Single Tone Excitation

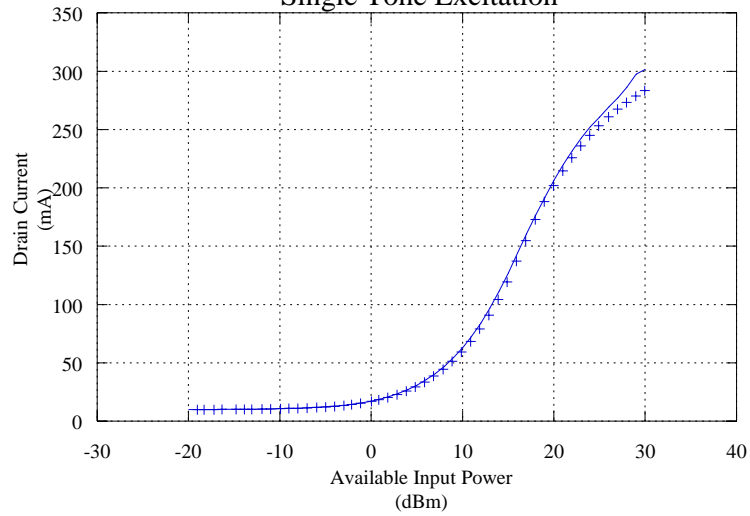


Drain Efficiency vs. Available Input Power  
 Single Tone Excitation

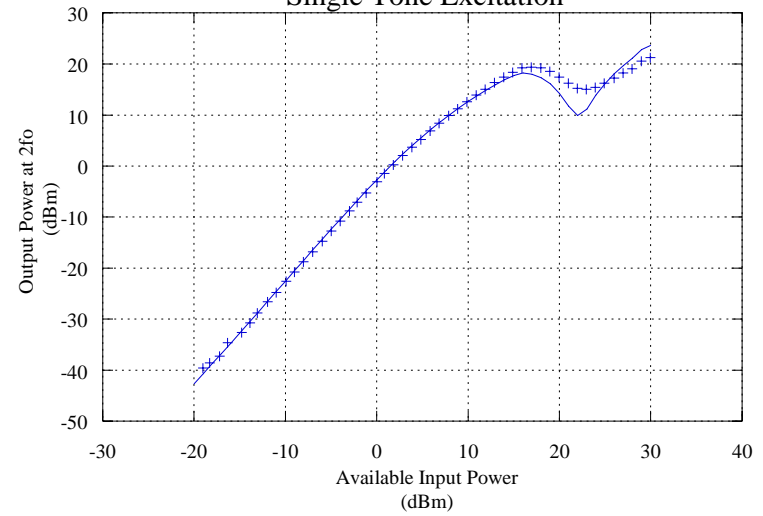


Tuned for Efficiency  
 Solid: Simulated & Points: Measured

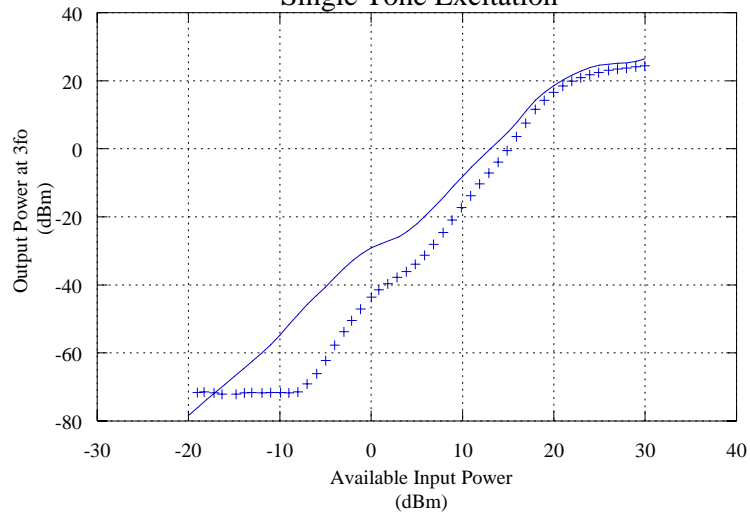
Drain Current vs. Available Input Power  
 Single Tone Excitation



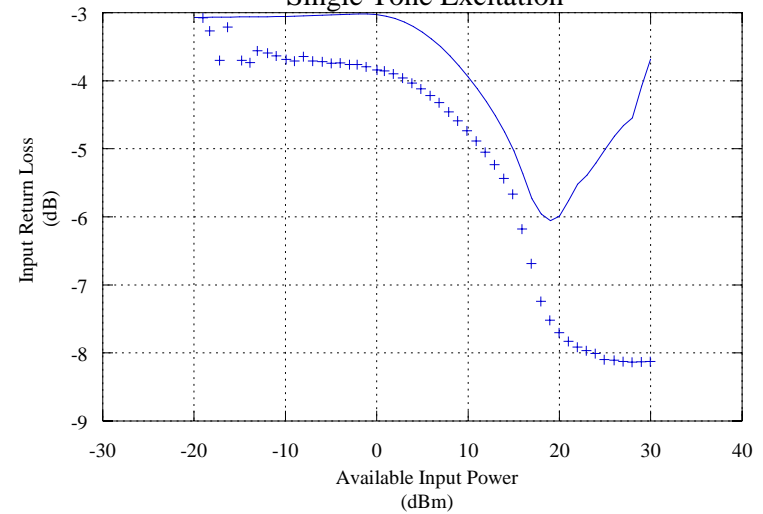
Output Power at 2fo vs. Available Input Power  
 Single Tone Excitation



Output Power at 3fo vs. Available Input Power  
 Single Tone Excitation



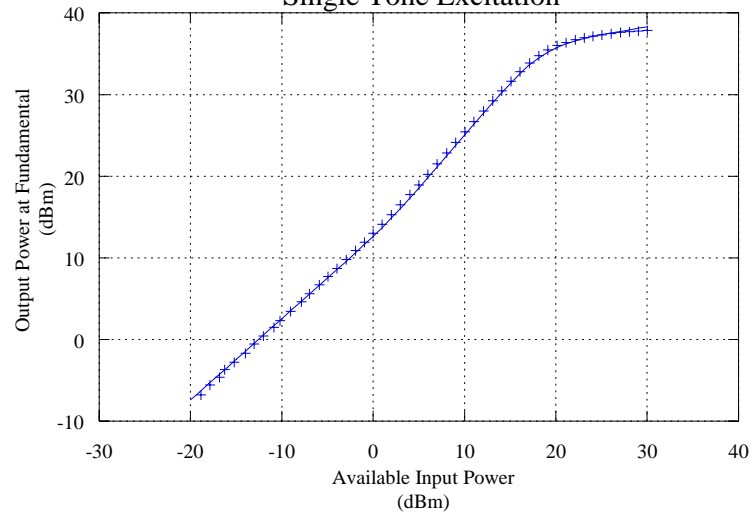
Input Return Loss vs. Available Input Power  
 Single Tone Excitation



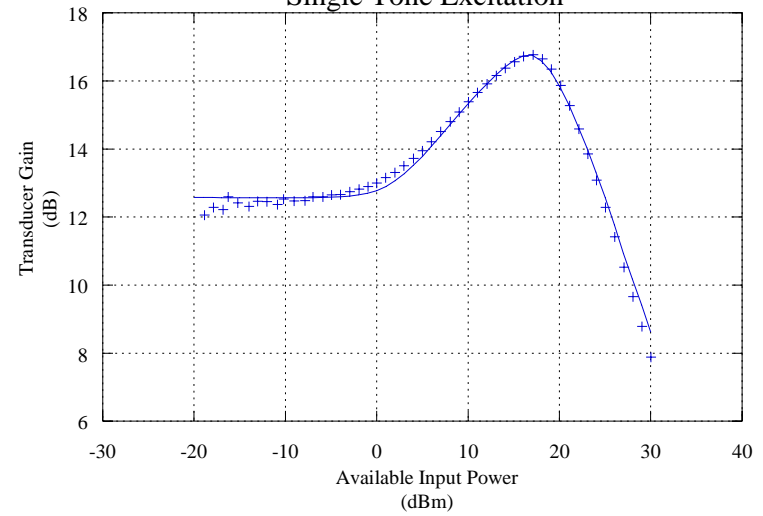
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm

Tuned for Power & Efficiency  
 Solid: Simulated & Points: Measured

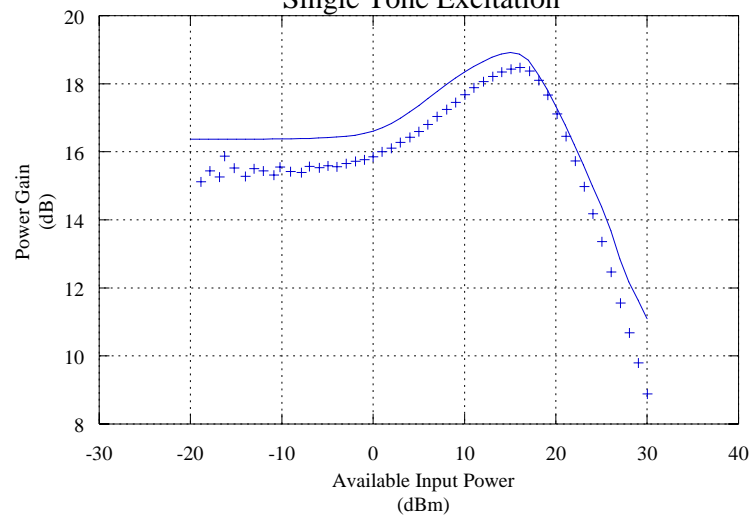
Output Power at Fundamental vs. Available Input Power  
 Single Tone Excitation



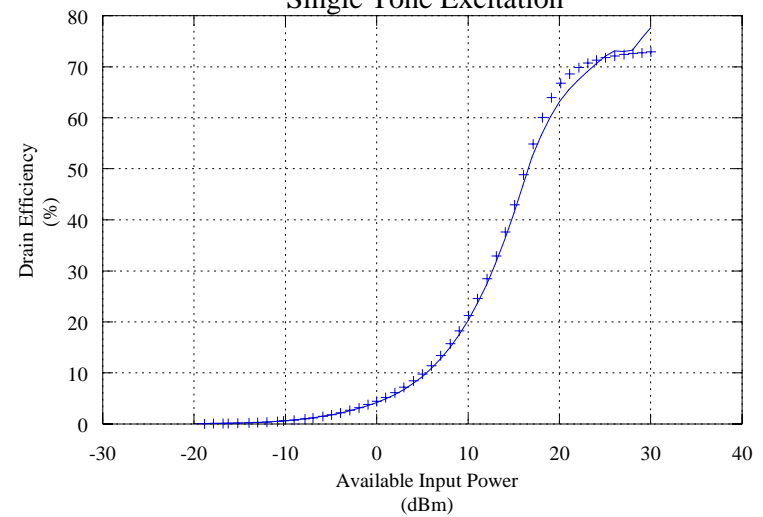
Transducer Gain vs. Available Input Power  
 Single Tone Excitation



Power Gain vs. Available Input Power  
 Single Tone Excitation



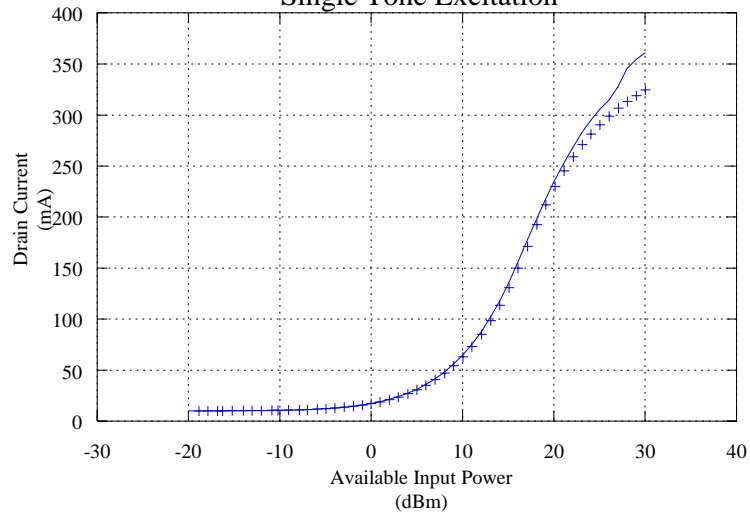
Drain Efficiency vs. Available Input Power  
 Single Tone Excitation



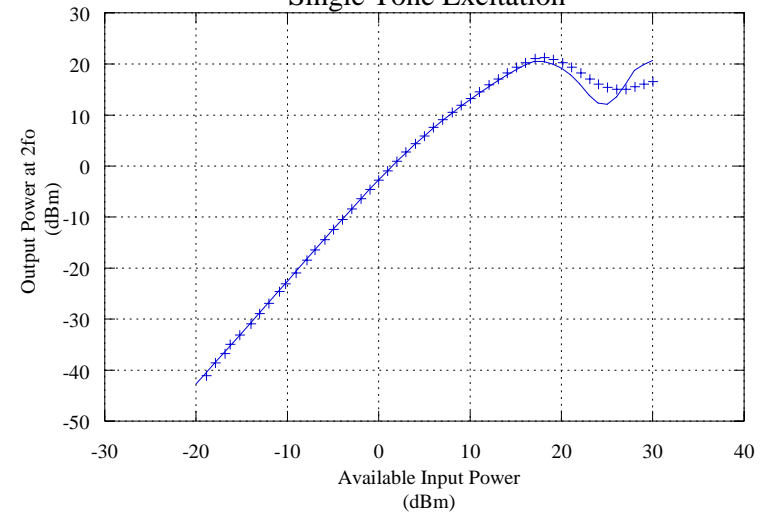
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm

Tuned for Power & Efficiency  
 Solid: Simulated & Points: Measured

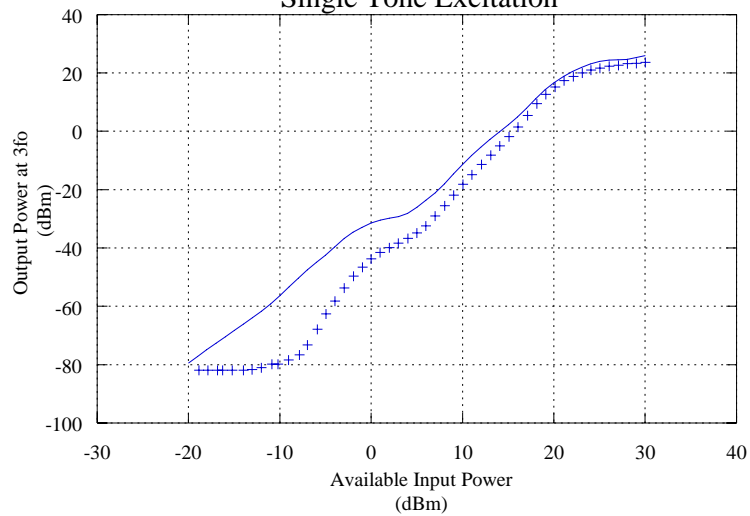
Drain Current vs. Available Input Power  
 Single Tone Excitation



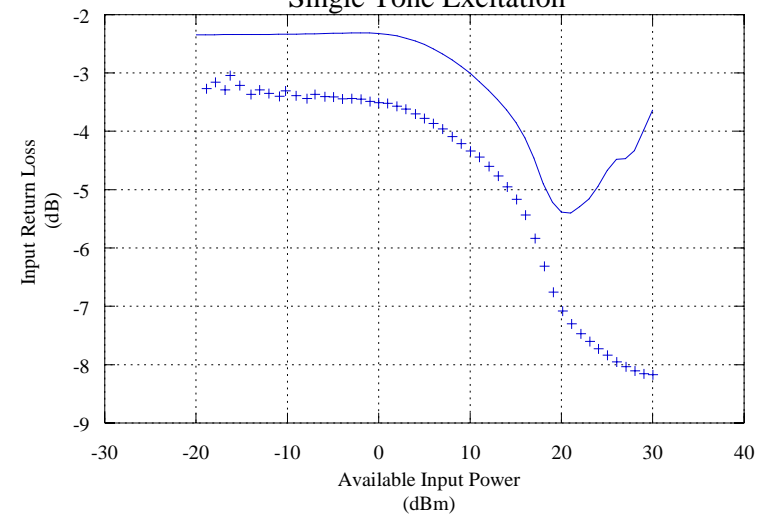
Output Power at 2fo vs. Available Input Power  
 Single Tone Excitation



Output Power at 3fo vs. Available Input Power  
 Single Tone Excitation



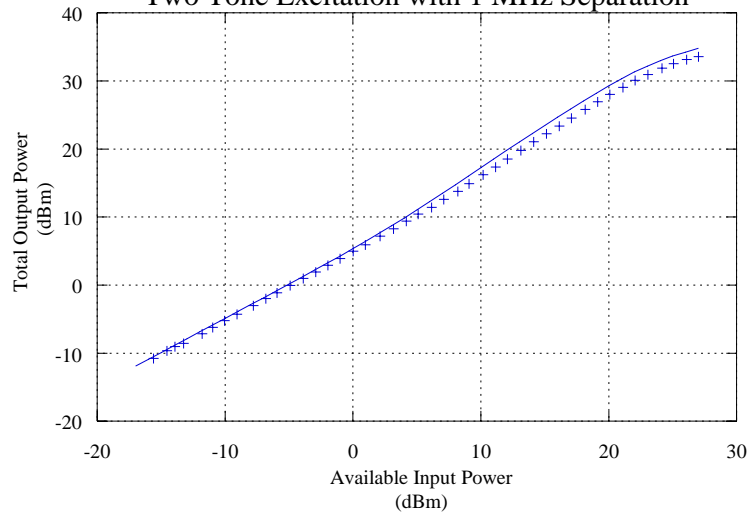
Input Return Loss vs. Available Input Power  
 Single Tone Excitation



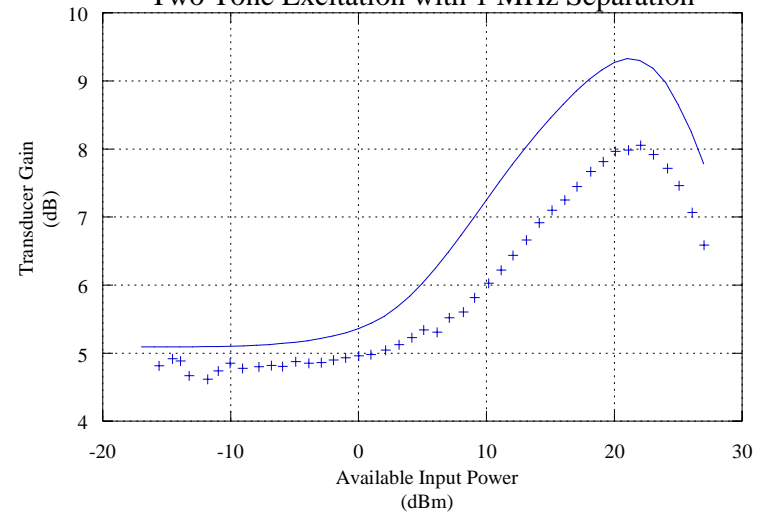


1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS} = 26$  v &  $I_{DS} = 2.0$  mA/mm  
 50 ohm Termination  
 Solid: Simulated & Points: Measured

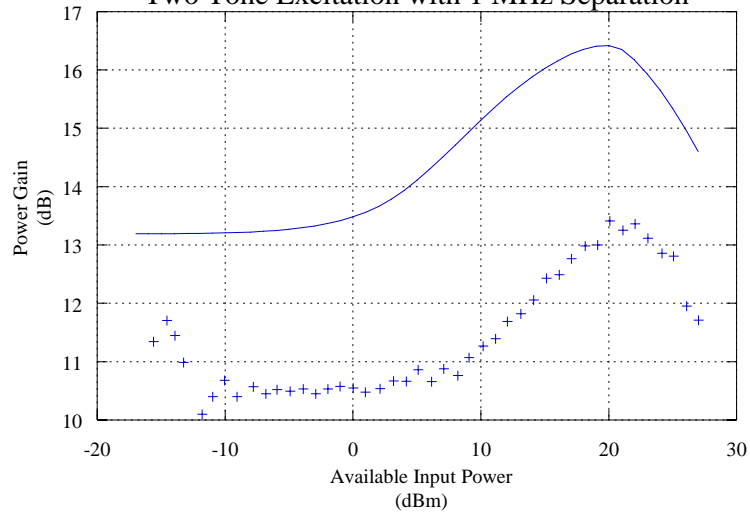
Total Output Power vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



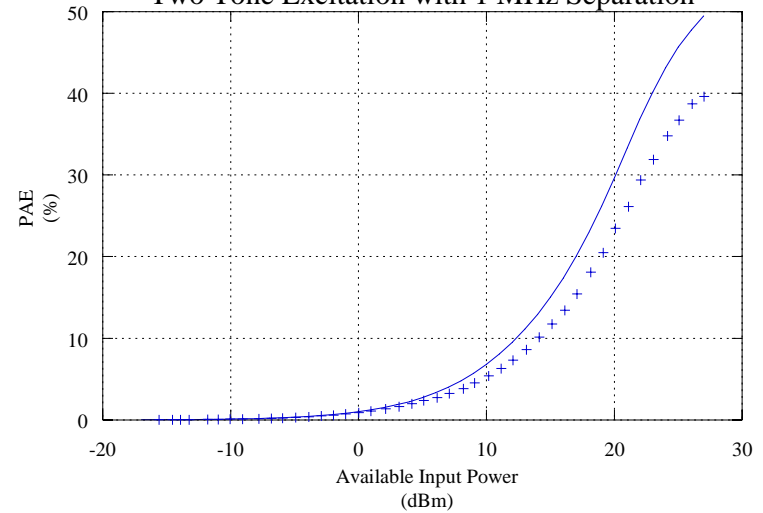
Transducer Gain vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation

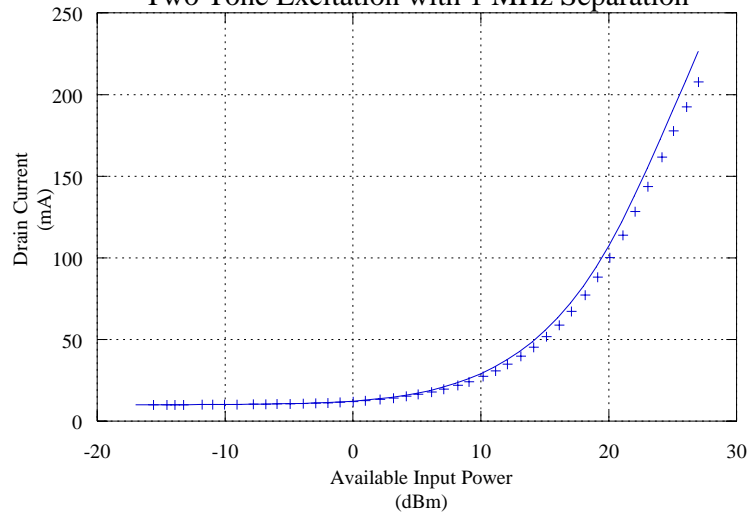


PAE vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation

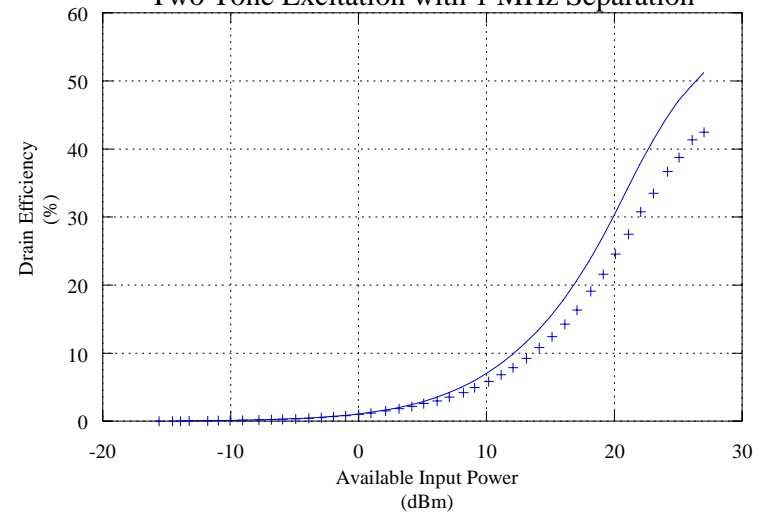


1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS} = 26$  v &  $I_{DS} = 2.0$  mA/mm  
 50 ohm Termination  
 Solid: Simulated & Points: Measured

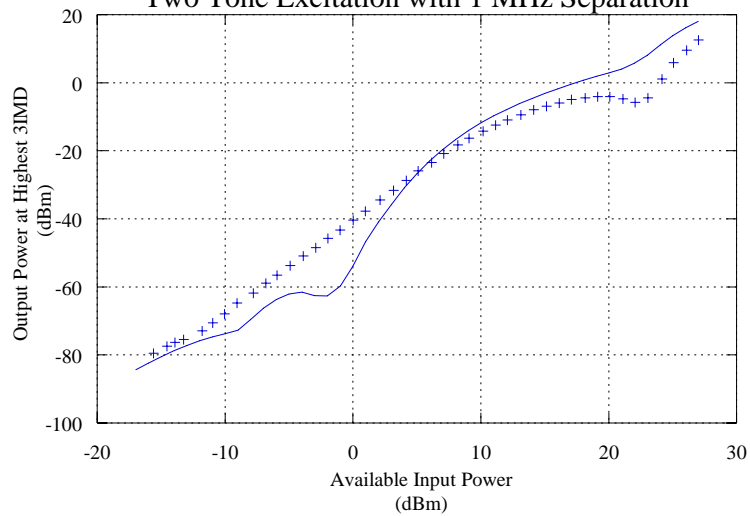
Drain Current vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



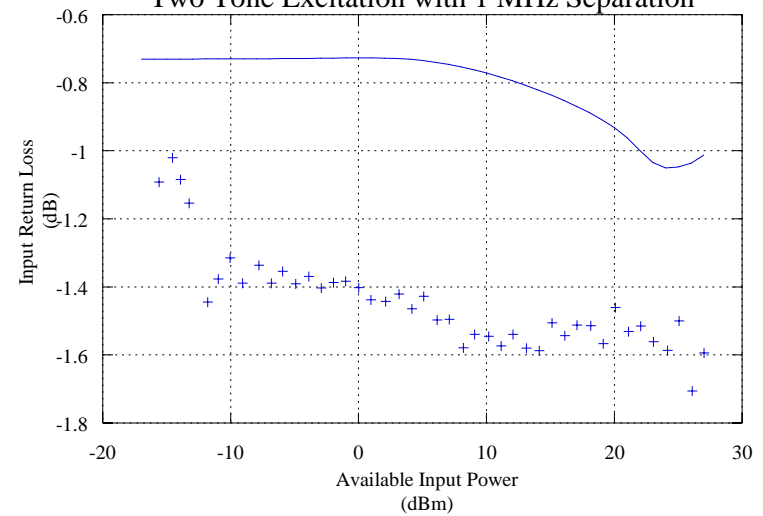
Drain Efficiency vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



Output Power at Highest 3IMD vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation

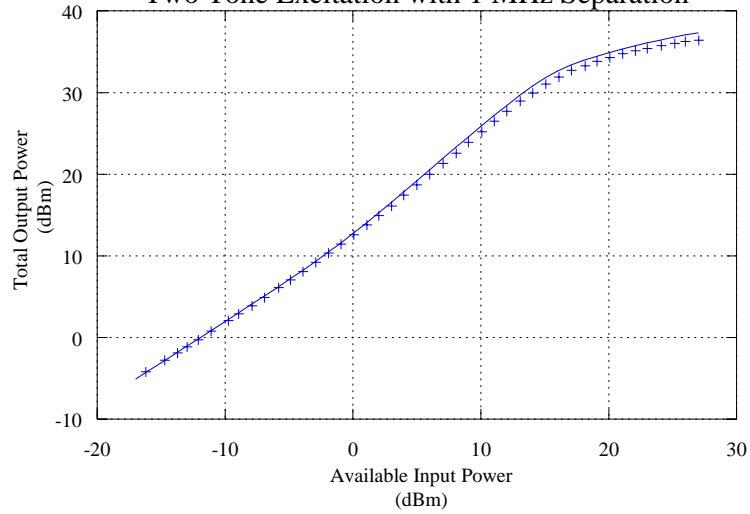


Input Return Loss vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation

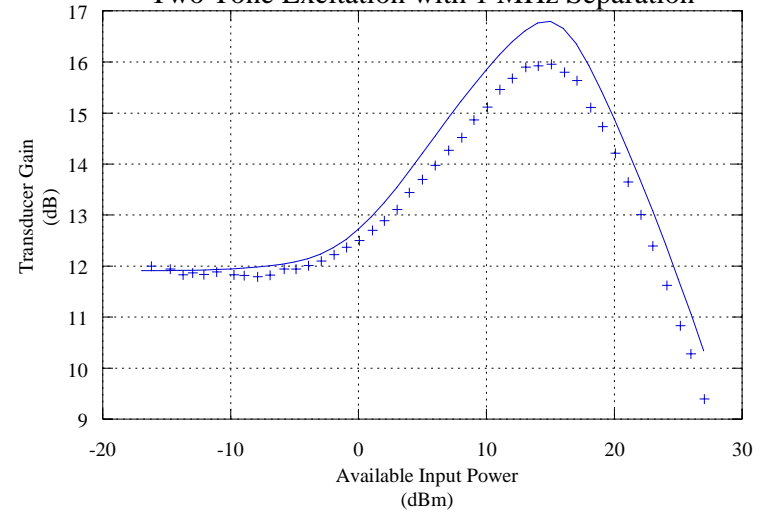


Tuned for Power  
 Solid: Simulated & Points: Measured

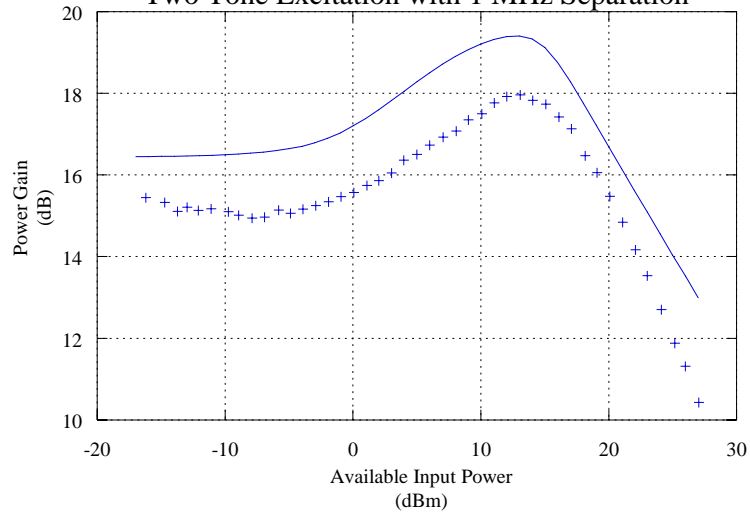
Total Output Power vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



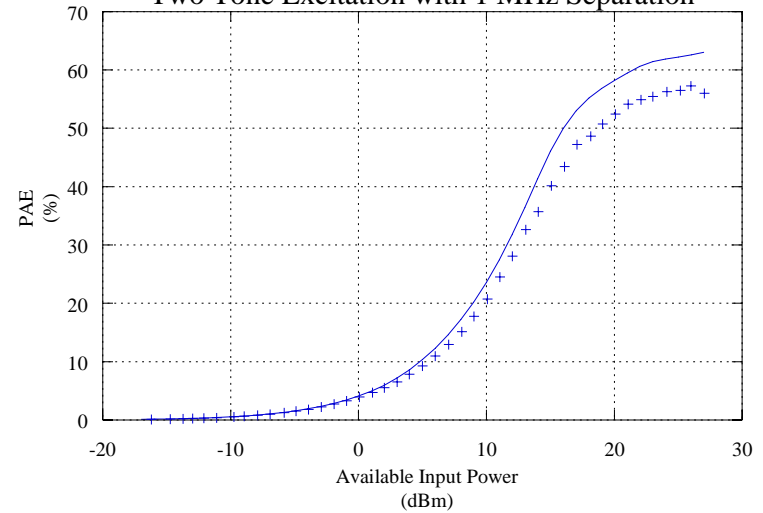
Transducer Gain vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



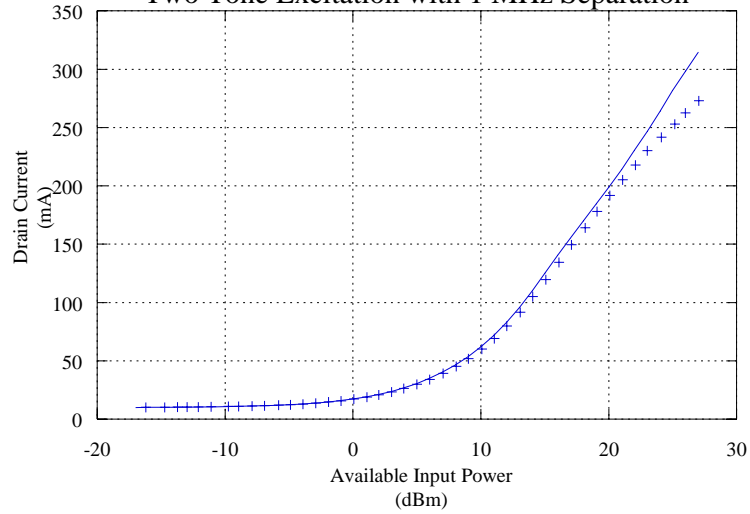
PAE vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



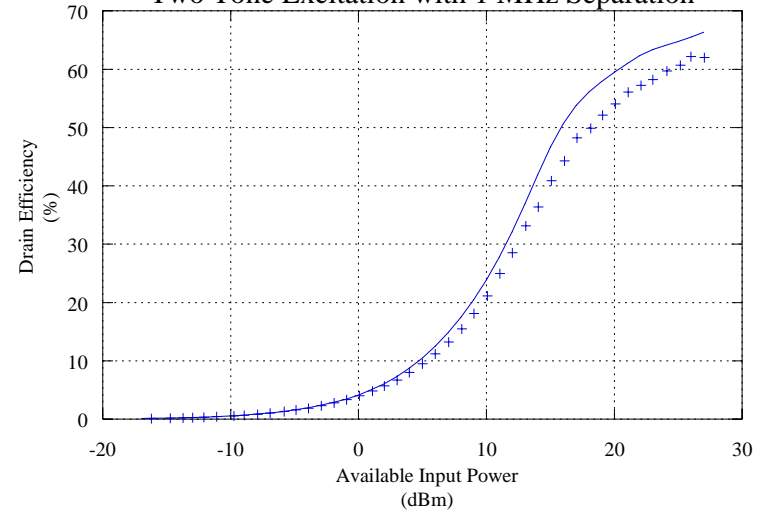
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS} = 26$  v &  $I_{DS} = 2.0$  mA/mm

Tuned for Power  
 Solid: Simulated & Points: Measured

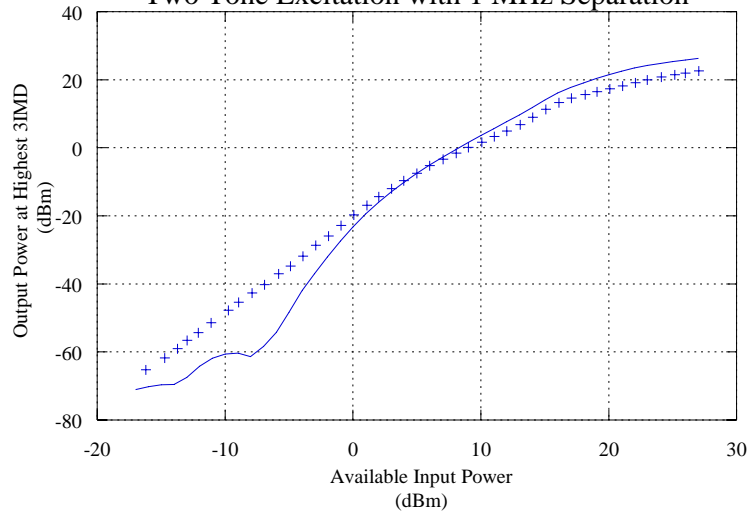
Drain Current vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



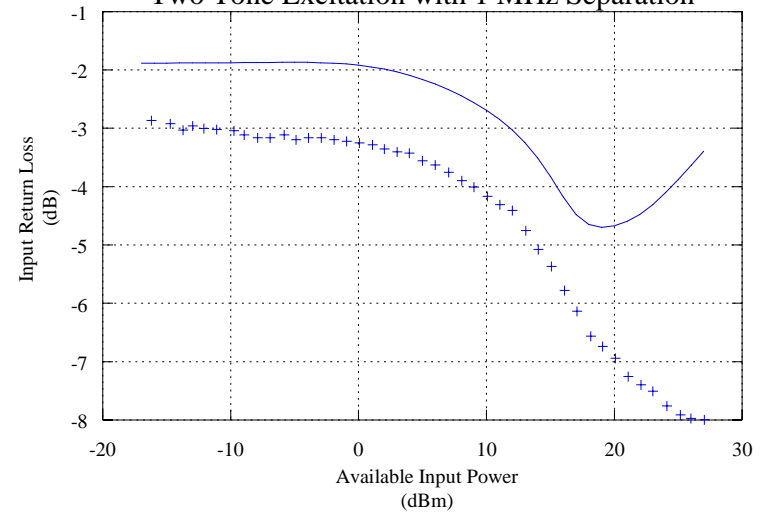
Drain Efficiency vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



Output Power at Highest 3IMD vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



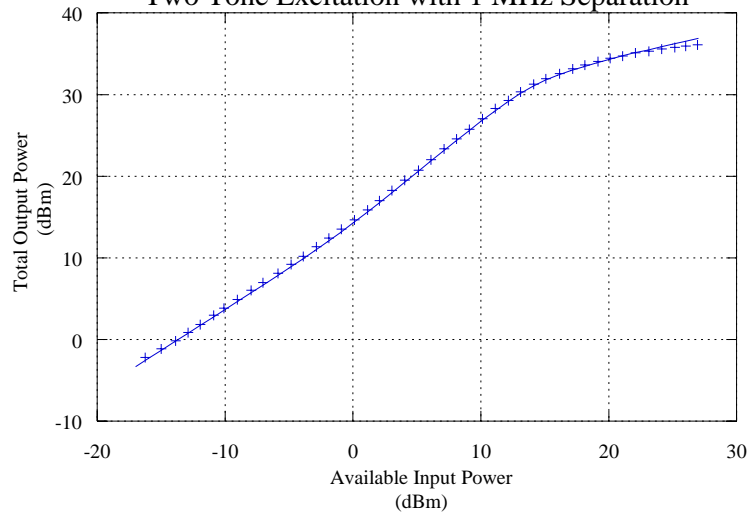
Input Return Loss vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



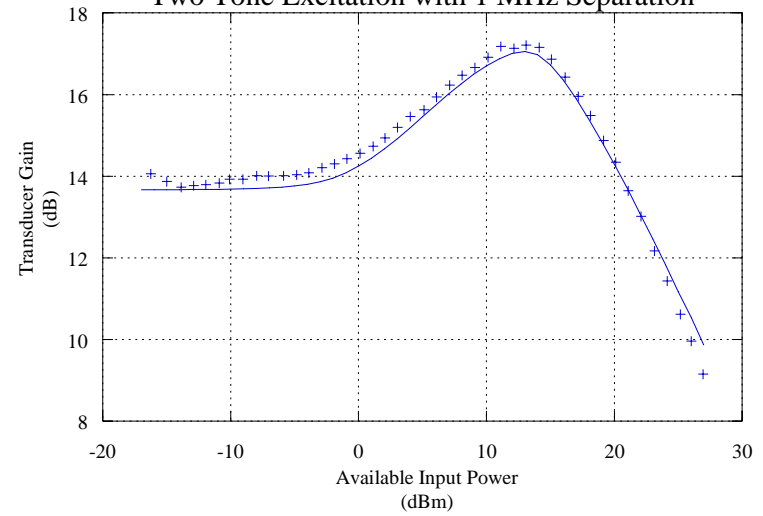
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm

Tuned for Efficiency  
 Solid: Simulated & Points: Measured

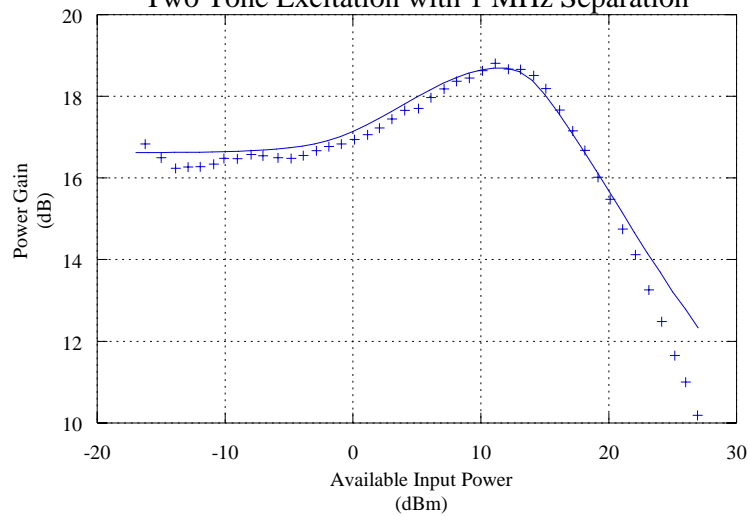
Total Output Power vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



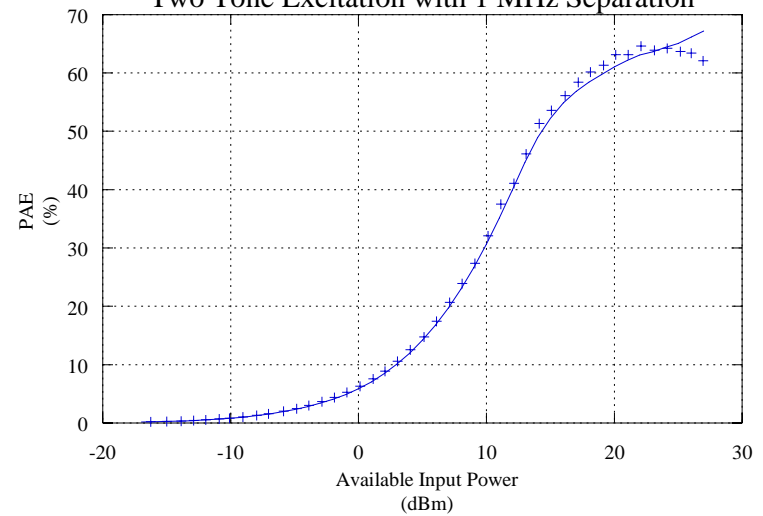
Transducer Gain vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



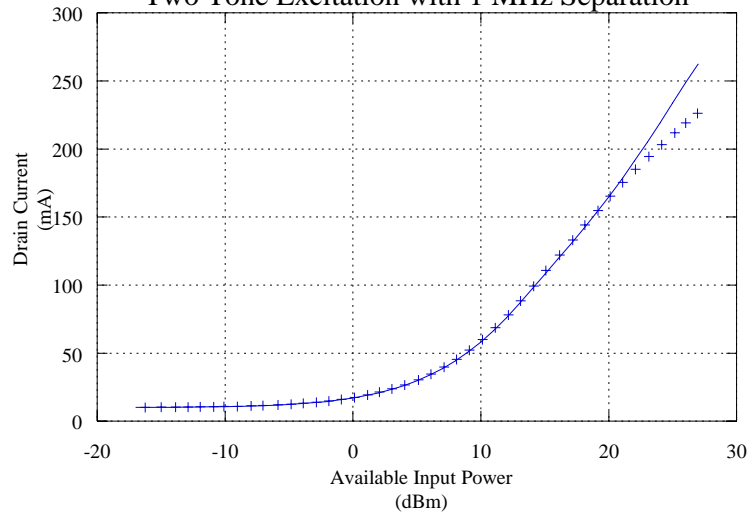
PAE vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



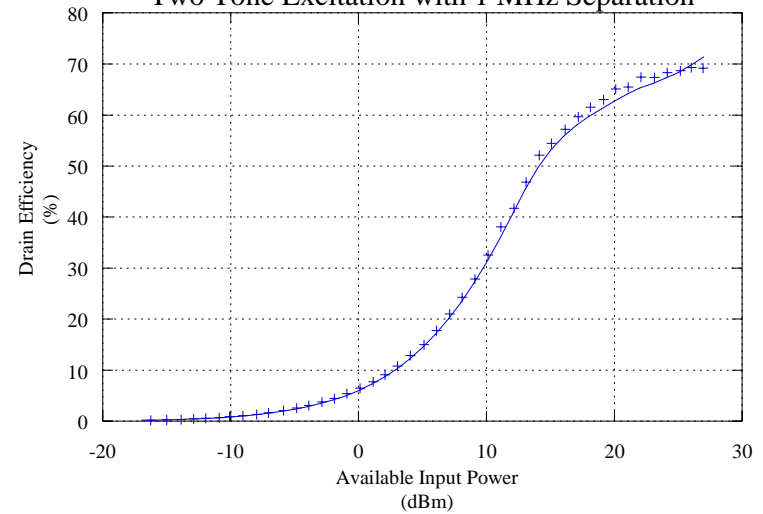
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm

Tuned for Efficiency  
 Solid: Simulated & Points: Measured

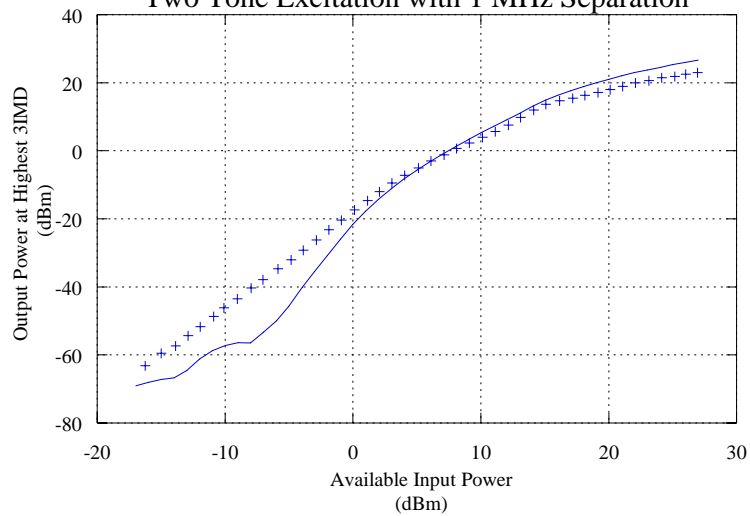
Drain Current vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



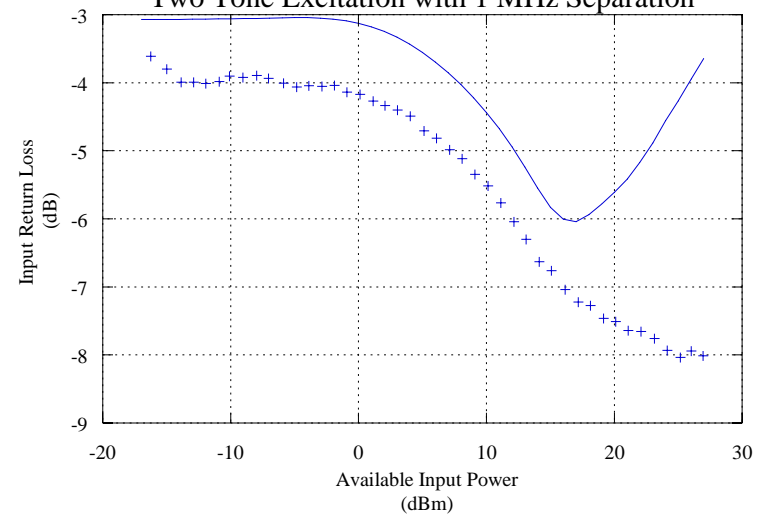
Drain Efficiency vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



Output Power at Highest 3IMD vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



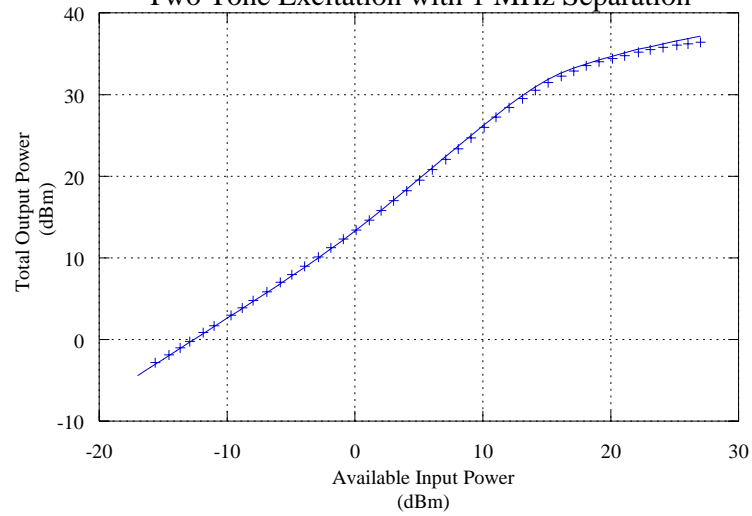
Input Return Loss vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



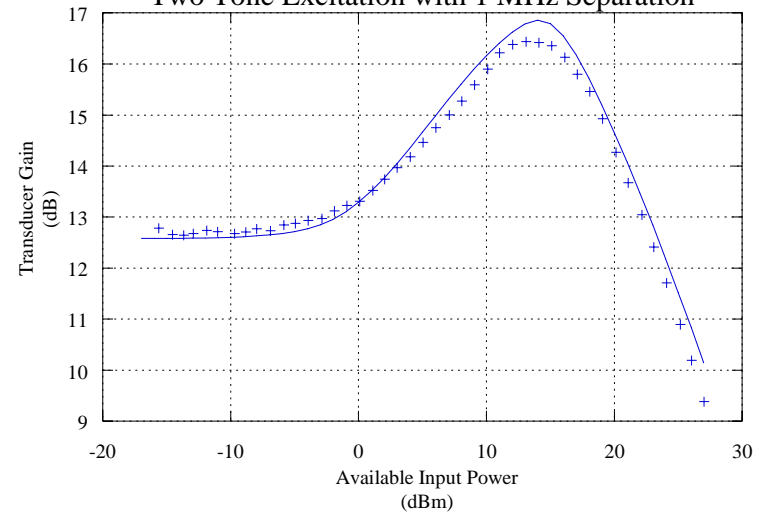
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS} = 26$  v &  $I_{DS} = 2.0$  mA/mm

Tuned for Power & Efficiency  
 Solid: Simulated & Points: Measured

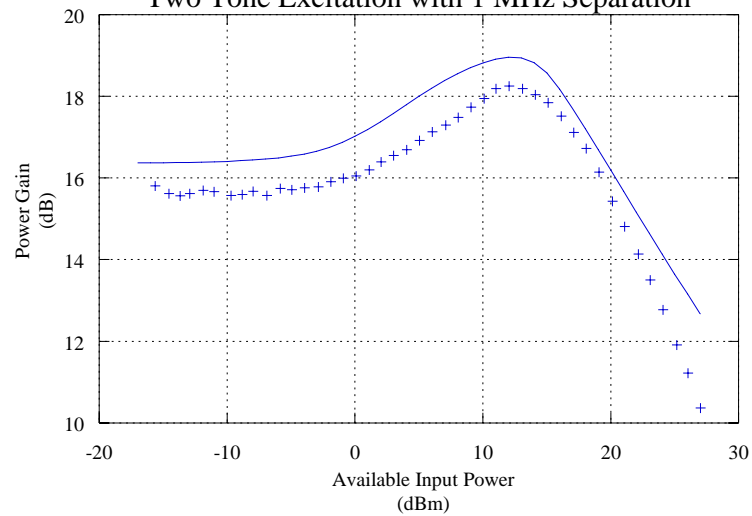
Total Output Power vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



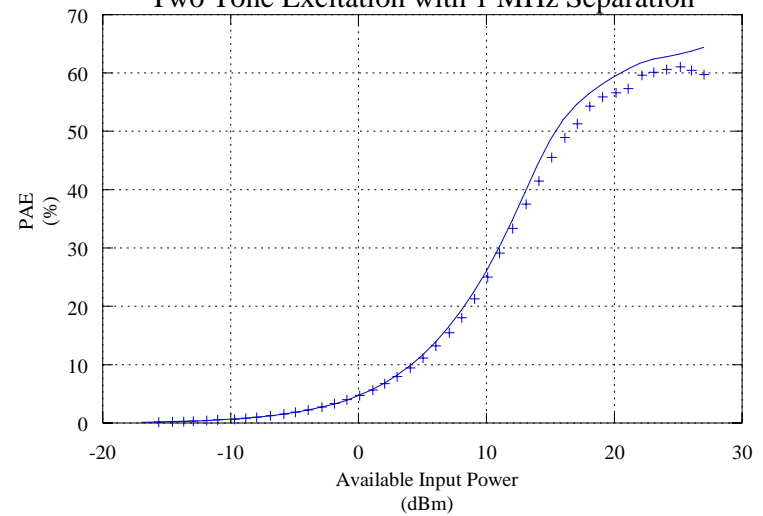
Transducer Gain vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



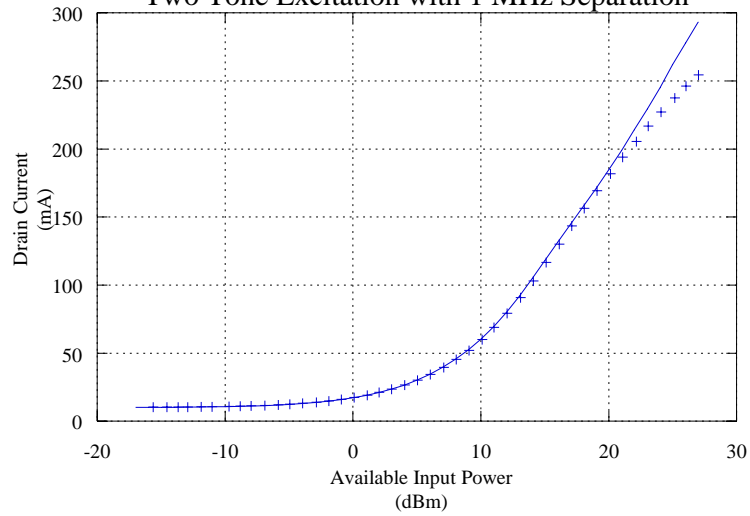
PAE vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



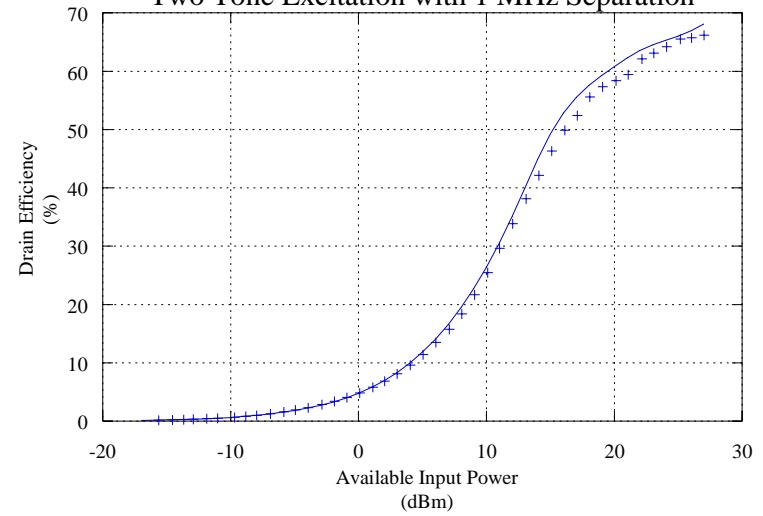
1 Block HV1 LDMOS Device  
 Number of fingers: 56, Periphery: 5.04 mm  
 Frequency: 1 GHz,  $V_{DS}=26$  v &  $I_{DS}=2.0$  mA/mm

Tuned for Power & Efficiency  
 Solid: Simulated & Points: Measured

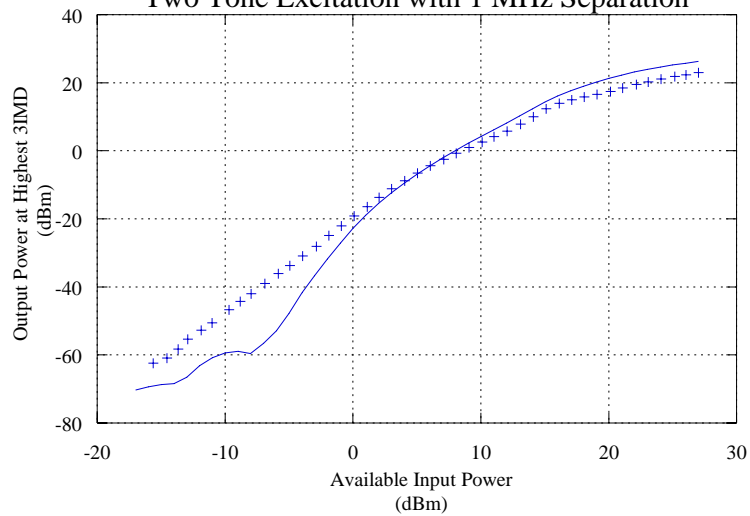
Drain Current vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



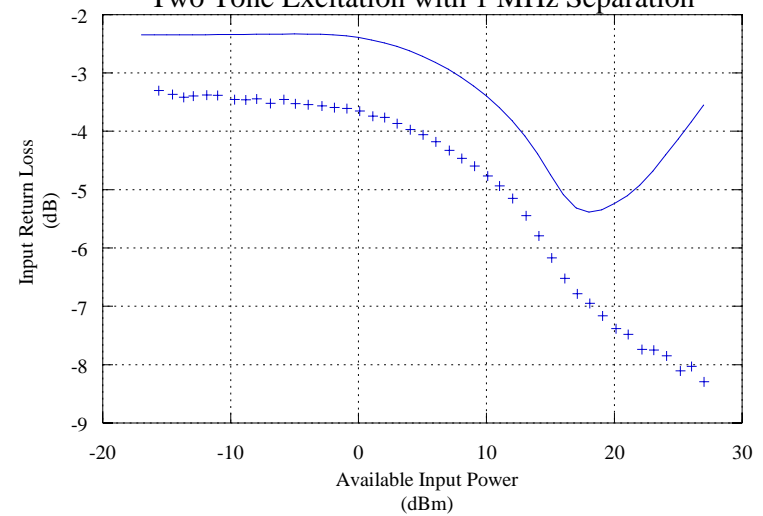
Drain Efficiency vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation




Output Power at Highest 3IMD vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation



Input Return Loss vs. Available Input Power  
 Two Tone Excitation with 1 MHz Separation





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